

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	Method of Selective Deposition of Heavily Doped Epitaxial SiGe
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Application Number : 10/683937



Confirmation Number: 2191

First Named Applicant: Yihwan Kim

Attorney Docket Number: AMAT8539TSGEPIRKK

Art Unit: 2812

Examiner:

Search string: (6559520 or 6335280 or 20030189208).pn

Certification: This Information Disclosure Statement was submitted under the following conditions, which satisfies the requirement under 37 CFR 1.97(e). The filer certified:

That no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6559520	2003-05-06	Matsuki et al.			
	2	6335280	2002-01-01	van der Jeugd			

US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
	1	20030189208	2003-10-09	Law et al.			

Signature

Examiner Name	Date
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